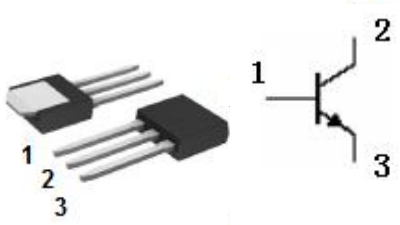
isc Silicon NPN Power Transistor 2SC3588

DESCRIPTION

- Low Collector Saturation Voltage-
  $V_{CE(sat)}$= 0.5V(Max)@ I_C= 300mA
- High Collector-Emitter Breakdown Voltage-
  $V_{(BR)CEO}$= 400V(Min)
- Complement to Type 2SA1400
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



pin 1.Base
2.Collector
3.Emitter

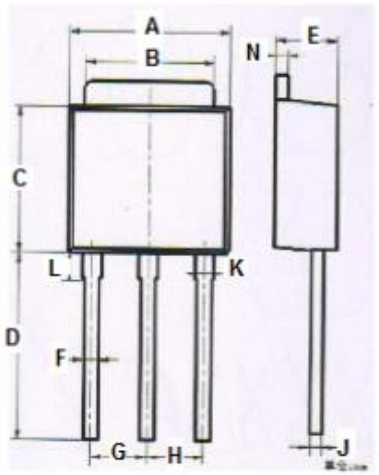
IPAK TO-251 package

APPLICATIONS

- Designed for high Voltage switching applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	500	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	0.5	A
I_{CM}	Collector Current-Pulse	1	A
P_C	Collector Power Dissipation @ T_C=25℃	2	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	6.40	6.48
B	5.10	5.50
C	5.80	6.20
D	9.20	9.60
E	2.20	2.40
F	0.50	0.70
G	2.09	2.49
H	2.09	2.49
J	0.40	0.60
K	0.70	0.90
L	1.60	2.00
N	0.40	0.60

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA ; I_B= 0	400			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 300mA; I_B= 60mA			0.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 300mA; I_B= 60mA			1.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 400V; I_E= 0			10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			10	μA
h_{FE-1}	DC Current Gain	I_C= 50mA ; V_{CE}= 5V	20		80	
h_{FE-2}	DC Current Gain	I_C= 0.3A ; V_{CE}= 5V	10			

◆ **h_{FE} Classifications**

M	L	K
20-40	30-60	40-80